

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

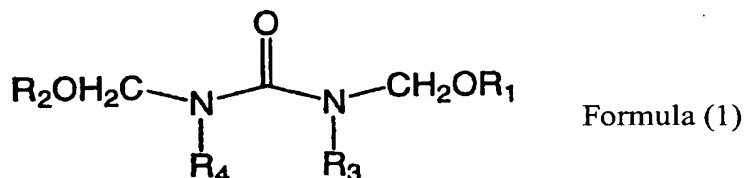
- 1-3. (Canceled)
4. (Currently Amended) The ~~anti-reflective coating forming composition process~~ for manufacturing a semiconductor device according to claim 11, wherein the anti-reflective coating forming composition further containing comprises a light absorbing compound and/or a light absorbing resin.
5. (Currently Amended) The ~~anti-reflective coating forming composition process~~ for manufacturing a semiconductor device according to claim 4, wherein the light absorbing compound is at least one compound selected from naphthalene compounds and anthracene compounds.
6. (Currently Amended) The ~~anti-reflective coating forming composition process~~ for manufacturing a semiconductor device according to claim 4, wherein the light absorbing compound is at least one compound selected from triazine compounds and triazine trione compounds.
7. (Currently Amended) The ~~anti-reflective coating forming composition process~~ for manufacturing a semiconductor device according to claim 4, wherein the light absorbing resin is a resin having in the structure at least one aromatic ring structure selected from benzene ring, naphthalene ring and anthracene ring.
8. (Currently Amended) The ~~anti-reflective coating forming composition process~~ for manufacturing a semiconductor device according to claim 11, wherein the anti-reflective coating forming composition further containing comprises a resin having at least one crosslink-forming substituent selected from hydroxy group, carboxy group, amino group and thiol group.

9-10. (Canceled)

11. (Currently Amended) A process for manufacturing a semiconductor device, characterized by comprising the steps of:

coating an anti-reflective coating forming composition ~~according to claim 1~~ on a substrate and baking it to form an anti-reflective coating;

wherein the anti-reflective coating forming composition comprises a compound of formula (1), a condensation product thereof or a resin produced from the compound



wherein R₁ and R₂ are independently of each other hydrogen atom or an alkyl group, R₃ and R₄ are independently of each other hydrogen atom, methyl group, ethyl group, hydroxymethyl group or an alkoxymethyl group, and an acid and/or acid generator, and the compound, the condensation product thereof or the resin produced from the compound is contained in an amount of 50 mass% or more in a solid content of the anti-reflective coating forming composition;

forming a photoresist on top of the anti-reflective coating;

exposing the substrate covered with the anti-reflective coating and the photoresist with a light;

developing it;

transferring an image on the substrate by etching to form an integrated circuit device.